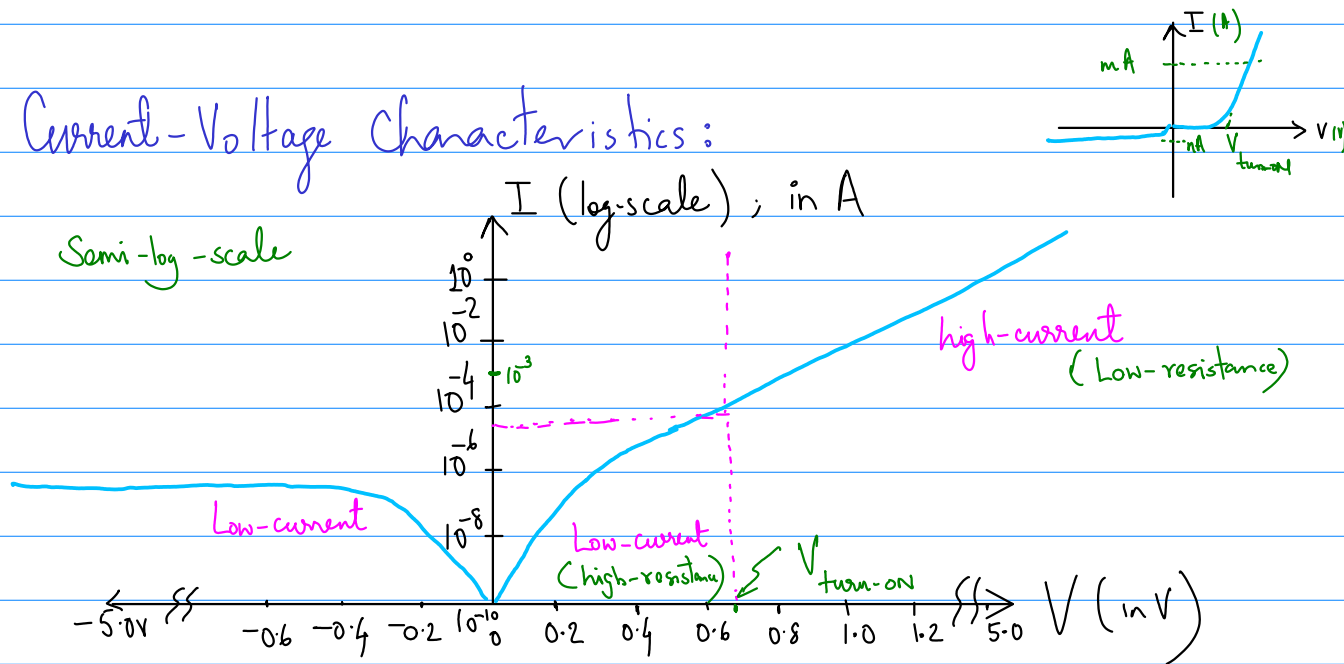


p-n Diode : Circuit Models

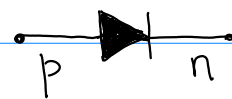
1. Current-Voltage Characteristics:



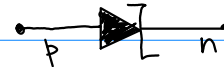
Conclusion: The current-voltage characteristics show two current levels:

- (i) Low when $V \leq V_{turn-on}$
- (ii) high when $V > V_{turn-on}$.

2) Circuit Model of a p-n diode:



ckt. symbol
of a p-n diode

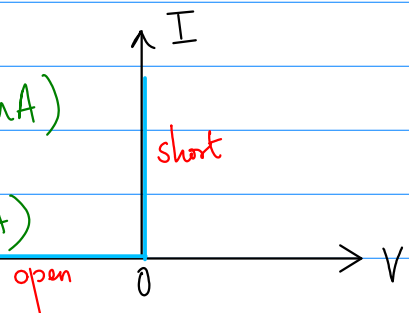


Zener diode

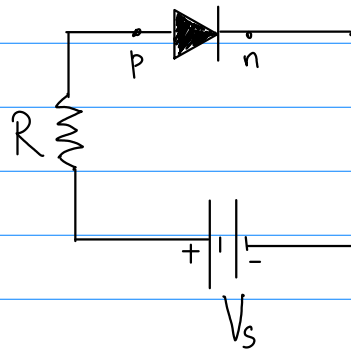
a) Ideal diode Model:

$V > 0$; $I \rightarrow \text{high (mA)}$

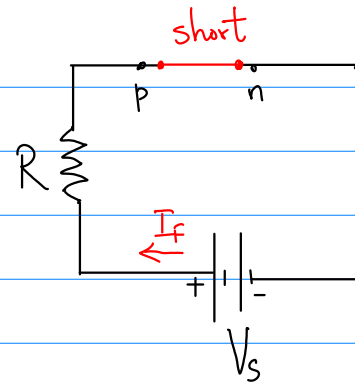
$V < 0$; $I \rightarrow \text{Low (}\mu\text{A)}$



(i) Forward bias

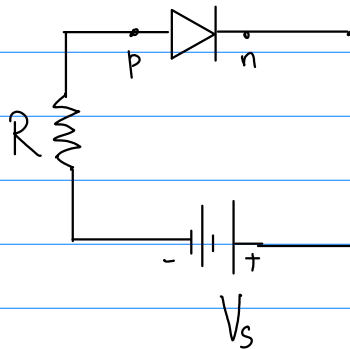


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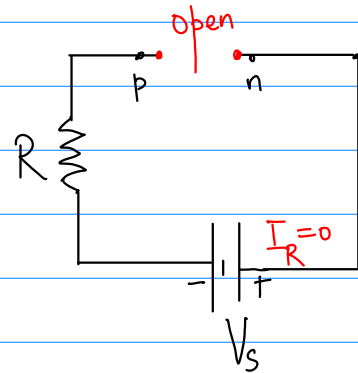


$$I_F = \frac{V_s}{R}$$

(ii) Reverse-bias:



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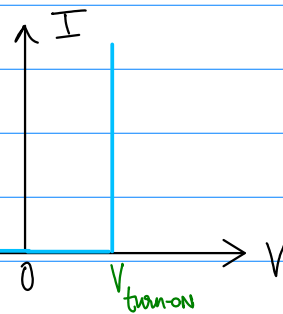


$$I_R = 0$$

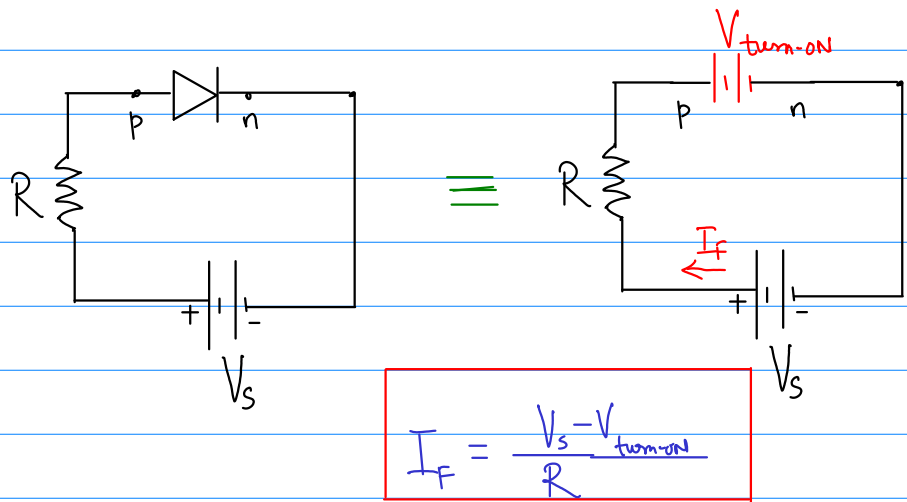
b) Modified Ideal Diode Model (Practical Model):

$V > V_{\text{turn-on}}$; $I \rightarrow \text{high (mA)}$

$V < V_{\text{turn-on}}$; $I \rightarrow \text{Low } (\mu\text{A})$



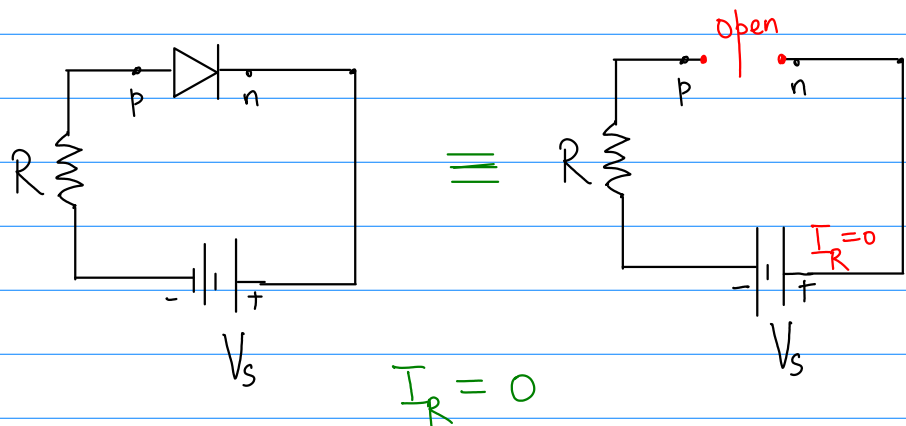
(i) Forward bias



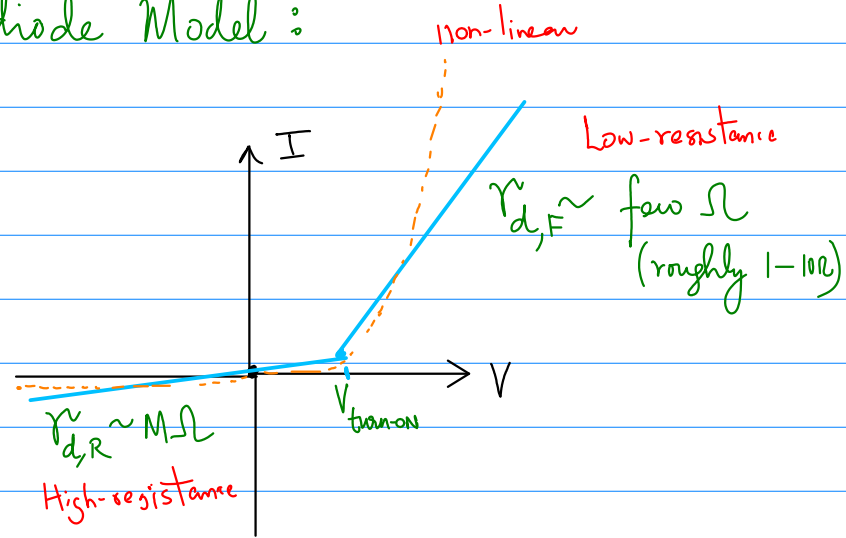
typically, for Silicon diode, $V_{\text{turn-on}} \sim 0.7V$

$$I_F = \frac{V_s - 0.7V}{R}$$

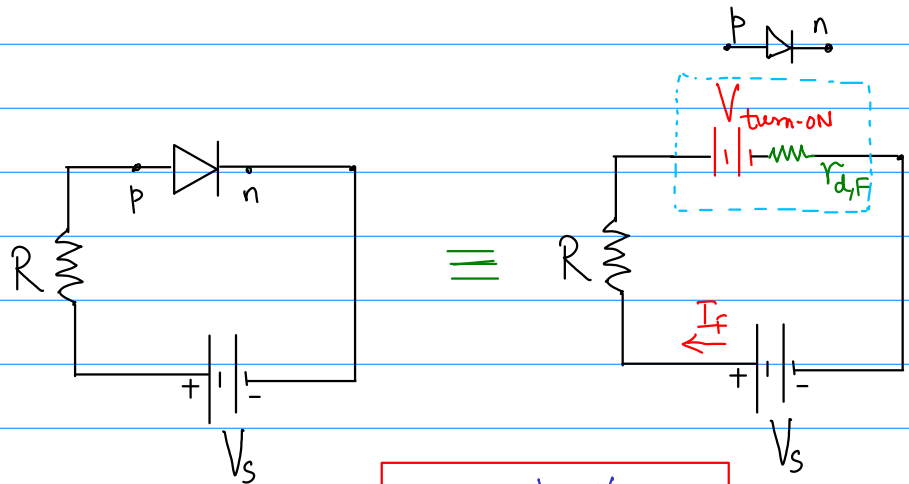
(ii) Reverse-bias:



3) Complete (Real) diode Model :

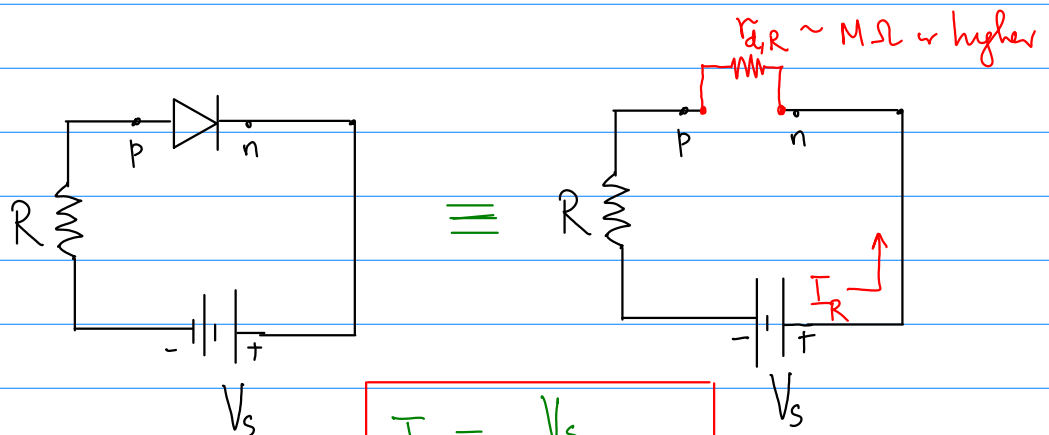


(i) Forward bias



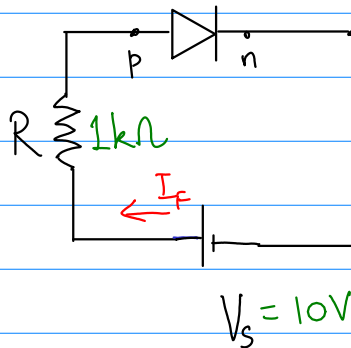
$$I_F = \frac{V_s - V_{\text{turn-on}}}{R + r_{d,F}}$$

(ii) Reverse-bias:



$$I_R = \frac{V_s}{R + r_{d,R}}$$

Example Problem:



Specification of the diode

$$V_{\text{turn-on}} = 0.6 \text{ V}$$

$$r_{d,F} = 10 \Omega$$

$$r_{d,R} = 100 \text{ k}\Omega$$

Let see forward-current (I_F) assuming the three models:

(i) Ideal model: Diode is replaced with "short".

$$I_F = \frac{V_s}{R} = \frac{10 \text{ V}}{1 \text{ k}\Omega} = \underline{10 \text{ mA}}$$

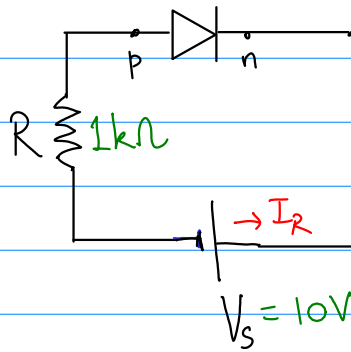
(ii) Modified Ideal Model: Diode is replaced with a "Voltage source" $= V_{\text{turn-on}}$

$$I_F = \frac{V_s - V_{\text{turn-on}}}{R} = \frac{10 \text{ V} - 0.6 \text{ V}}{1 \text{ k}\Omega} = \underline{9.4 \text{ mA}}$$

(iii) Real diode model: Diode is replaced with a voltage source and a resistor $r_{d,F}$

$$I_F = \frac{V_s - V_{\text{turn-on}}}{R + r_{d,F}} = \frac{10 \text{ V} - 0.6 \text{ V}}{1 \text{ k}\Omega + 10 \Omega}$$

$$I_F = \underline{9.3 \text{ mA}}$$



(i) Ideal Model : $I_R = 0$ (diode \equiv open)

(ii) M.I.M. : $I_R = 0$ (open)

(iii) Real Model :

Diode is replaced
with a resistor
' $r_{d,R}$ '

$$I_R = \frac{V_s}{R + r_{d,R}} = \frac{10V}{1k\Omega + 100k\Omega}$$

$$I_R = 100\mu A$$